PLUS Search Results for S/N 09/920,927, Searched December 10, 2001 (Top 50)

6165873	6235627	5492850	5516719	6235572
6072241	6248654	5654567	5721154	4606011
6140673	6271573	6069038	5789289	4786954
6200855	6071 <b>7</b> 99	6150183	5850091	4873559
6218235	6091154	5017982	5885865	4894695
6218235	6211047	5260600	5943582	4956692
6251721	6211047	5362686	6033967	4970564
6287914	5670431	5447881	6066538	4974040
6204161	5451539	5447882	6087217	4985368
6078073	5468671	5470776	6103571	5021357

## Most Frequently Occurring Classifications of Patents Returned From A Search of 09/920,927 on December 10, 2001

## **Combined Classifications**

- 16 438/396
- 11 438/253
- 7 257/306
- 6 438/397
- 5 257/301
- 5 438/241
- 4 257/758
- 4 438/255
- 4 438/738
- 3 148/DIG 14
- 3 365/149
- 3 438/240
- 3 438/254
- 3 438/398
- 3 438/595
- 3 438/618
- 2 257/296
- 2 257/297
- 2 257/303
- 2 257/770
- 2 438/248
- 2 438/2562 438/258
- 2 438/393
- 2 438/533
- 2 438/587
- 2 438/597
- 2 438/624
- 2 438/656
- 2 438/785

```
(7 OR, 9 XR)
16 438/396
                  438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
          Class
                        MAKING PASSIVE DEVICE (E.G., RESISTOR,
          438/381
                            CAPACITOR, ETC.)
                        .Stacked capacitor
          438/396
                   (4 \text{ OR}, 7 \text{ XR})
 11 438/253
                  438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
                        MAKING FIELD EFFECT DEVICE HAVING PAIR OF
          438/142
                                ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY
FORMATION OR
                                ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
                         .Having insulated gate (e.g., IGFET, MISFET,
          438/197
                              MOSFET, etc.)
                         .. Including passive device (e.g., resistor,
          438/238
                              capacitor, etc.)
                         ... Capacitor
          438/239
                         ....Stacked capacitor
          438/253
                   (4 \text{ OR}, 3 \text{ XR})
  7 257/306
                  257 : ACTIVE SOLID-STATE DEVICES
          Class
                        FIELD EFFECT DEVICE
          257/213
                        .Having insulated electrode (e.g., MOSFET, MOS
          257/288
                              diode)
                         .. Insulated gate capacitor or insulated gate
          257/296
                             transistor combined with capacitor (e.g., dynamic
memory
                             cell)
                         ...Stacked capacitor
          257/306
                   (0 OR, 6 XR)
  6 438/397
                  438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
          Class
                        MAKING PASSIVE DEVICE (E.G., RESISTOR,
          438/381
                              CAPACITOR, ETC.)
                         .Stacked capacitor
          438/396
                         .. Including selectively removing material to
          438/397
                            undercut and expose storage node layer
                   (2 OR, 3 XR)
  5 257/301
                  257 : ACTIVE SOLID-STATE DEVICES
          Class
                         FIELD EFFECT DEVICE
          257/213
                         .Having insulated electrode (e.g., MOSFET, MOS
          257/288
                              diode)
                         .. Insulated gate capacitor or insulated gate
          257/296
                             transistor combined with capacitor (e.g., dynamic
memory
                             cell)
                         ... Capacitor in trench
          257/301
                    (3 OR, 2 XR)
    438/241
                   438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
          Class
                         MAKING FIELD EFFECT DEVICE HAVING PAIR OF
          438/142
```

ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS 438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.) .. Including passive device (e.g., resistor, 438/238 capacitor, etc.) ... Capacitor 438/239 438/241 ....And additional field effect transistor (e.g., sense or access transistor, etc.) (0 OR, 4 XR)257/758 257 : ACTIVE SOLID-STATE DEVICES Class 257/734 COMBINED WITH ELECTRICAL CONTACT OR LEAD .Of specified material other than unalloyed 257/741 aluminum ..Layered 257/750 257/758 ... Multiple metal levels on semiconductor, separated by insulating layer (e.g., multiple level metallization for integrated circuit) (3 OR, 1 XR)4 438/255 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS MAKING FIELD EFFECT DEVICE HAVING PAIR OF 438/142 ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS .Having insulated gate (e.g., IGFET, MISFET, 438/197 MOSFET, etc.) .. Including passive device (e.g., resistor, 438/238 capacitor, etc.) 438/239 ... Capacitor ....Stacked capacitor 438/253 .....Including texturizing storage node layer 438/255 438/738 (0 OR, 4 XR) Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS 438/689 CHEMICAL ETCHING 438/706 .Vapor phase etching (i.e., dry etching) ..Differential etching of semiconductor 438/735 substrate ... Substrate possessing multiple layers 438/737 .... Selectively etching substrate possessing 438/738 multiple layers of differing etch characteristics (0 OR, 3 XR)148/DIG 14 148 : METAL TREATMENT Class CAPACITOR 148/DIG 14 (1 OR, 2 XR) 365/149 365 : STATIC INFORMATION STORAGE AND RETRIEVAL Class SYSTEMS USING PARTICULAR ELEMENT 365/129 365/149 .Capacitors